

GaAlAs T-1 PACKAGE INFRARED EMITTING DIODE

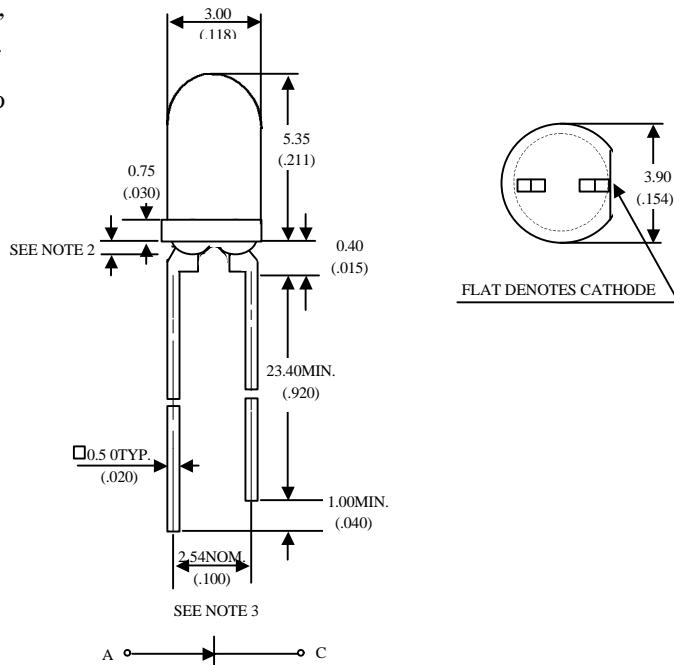
MIE-334H4

Description

The MIE-334H4 is a GaAlAs infrared LED having a peak wavelength at 850nm. It features ultra-high power, high response speed and molded package with higher radiant intensity. In addition to improving the S/N ratio in applied optical systems, the MIE-334H4 has greatly improved long-distance characteristics as well as significantly increased its range of applicability .

Package Dimensions

Unit : mm (inches)



Features

- Ultra-High radiant intensity
- High response speed
- Standard T-1 (φ3mm) package, radiant angle : 30°
- Peak wavelength $\lambda_p = 850$ nm
- Good spectral matching to si-photodetector

Application

- Data communication
- SIR

Absolute Maximum Ratings

@ $T_A=25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current(300pps,10μs pulse)	1	A
Continuos Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

Optical-Electrical Characteristics

@ $T_A=25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	$I_F=20\text{mA}$	I_e		3.2		mW/sr
Forward Voltage	$I_F=50\text{mA}$	V_F		1.5	1.8	V
Reverse Current	$V_R=5\text{V}$	I_R			100	μA
Peak Wavelength	$I_F=20\text{mA}$	λ		850		nm
Spectral Bandwidth	$I_F=20\text{mA}$	$\Delta\lambda$		30		nm
View Angle	$I_F=20\text{mA}$	$2\theta_{1/2}$		30		deg .

Typical Optical-Electrical Characteristic Curves

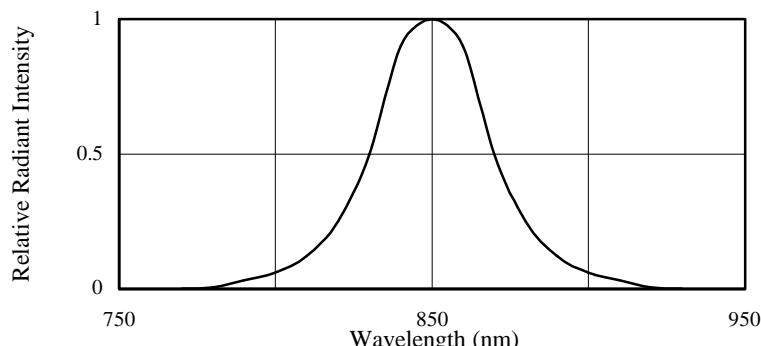


FIG.1 SPECTRAL DISTRIBUTION

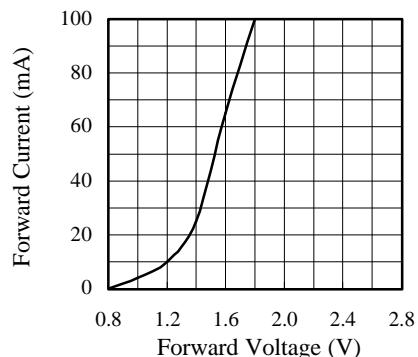


FIG.2 FORWARD CURRENT VS.
FORWARD VOLTAGE

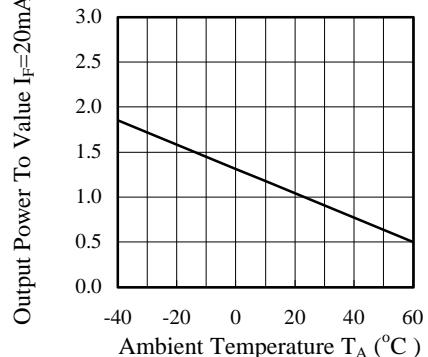


FIG.3 RELATIVE RADIANT INTENSITY
VS. AMBIENT TEMPERATURE

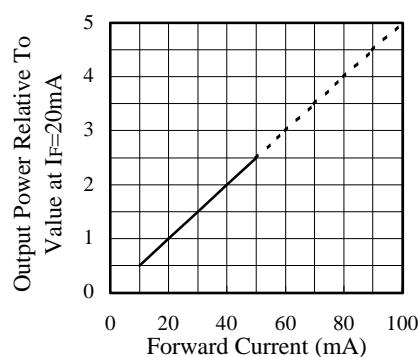


FIG.4 RELATIVE RADIANT INTENSITY
VS. FORWARD CURRENT

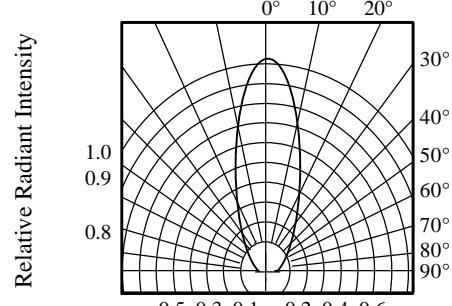


FIG.5 RADIATION DIAGRAM